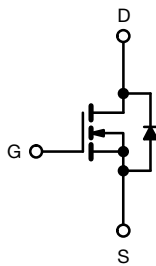
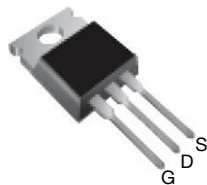


## E Series Power MOSFET

**TO-220AB**


N-Channel MOSFET

### FEATURES

- 4<sup>th</sup> generation E series technology
- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low effective capacitance ( $C_{o(er)}$ )
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Kelvin connection for reduced gate noise
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Solar (PV inverters)

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	700	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.106
$Q_g$ max. (nC)	57	
$Q_{gs}$ (nC)	15	
$Q_{gd}$ (nC)	14	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free and halogen-free	SiHP125N65E-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	650	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	60	
Linear derating factor		1.67	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	81	mJ
Maximum power dissipation	$P_D$	208	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dv/dt$	100	V/ns
Reverse diode $dv/dt$ <sup>c</sup>		7.1	


#### Notes

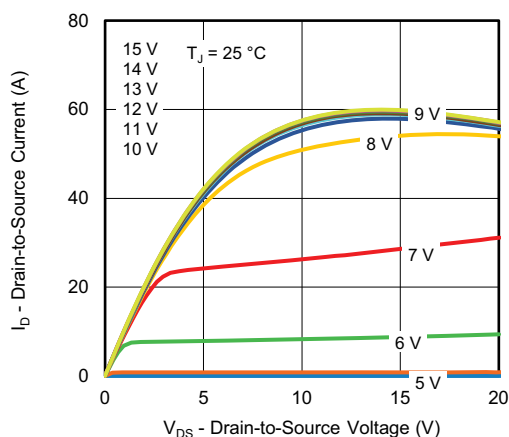
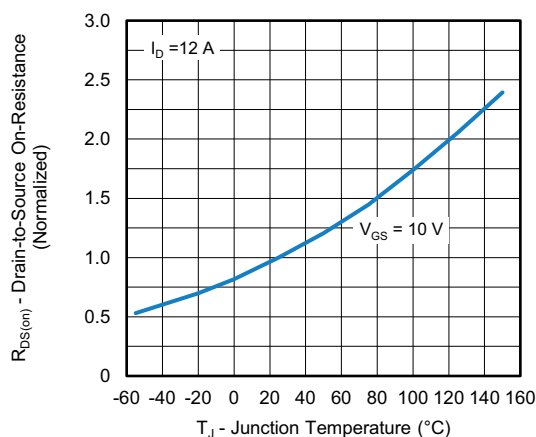
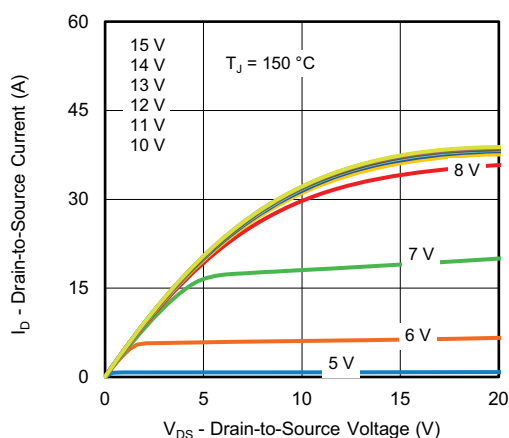
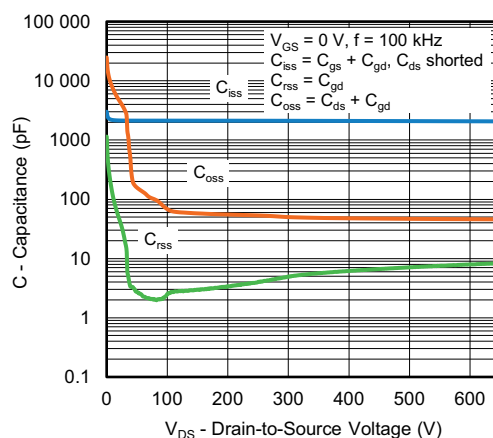
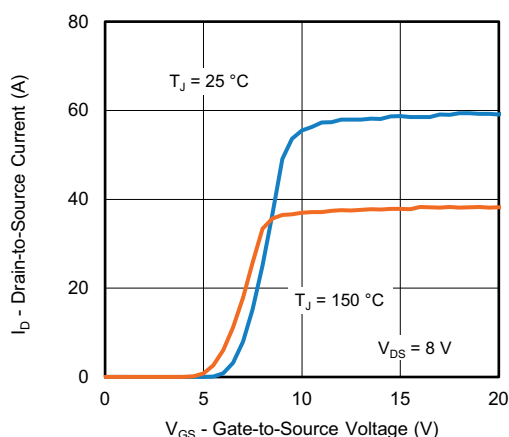
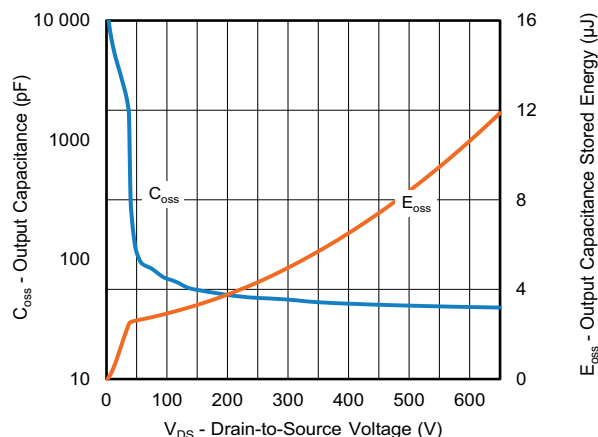
- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 2.4$  A
- $I_{SD} \leq I_D$ ,  $di/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C

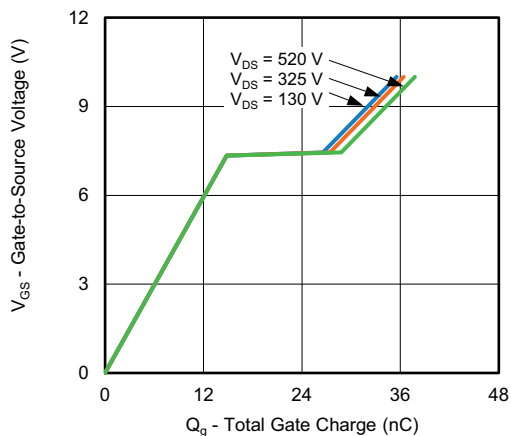
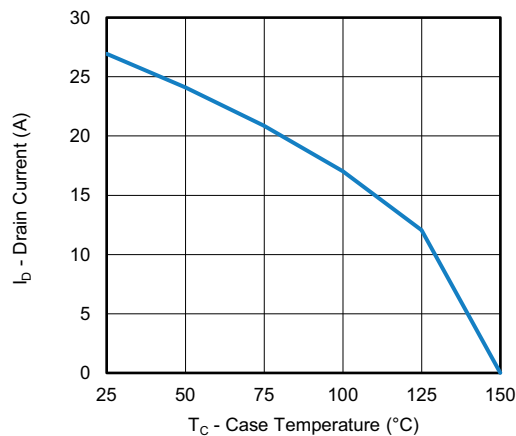
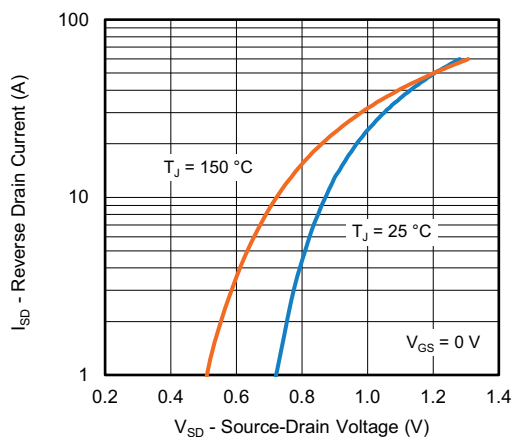
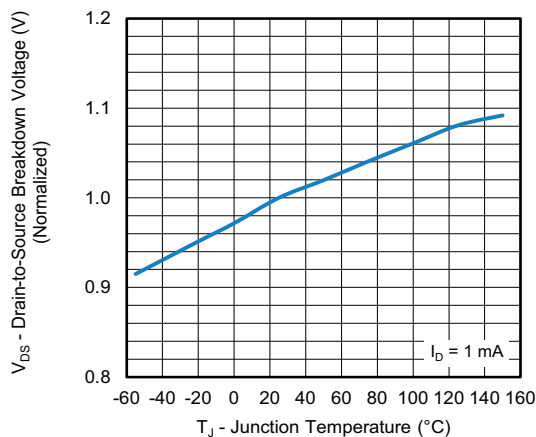
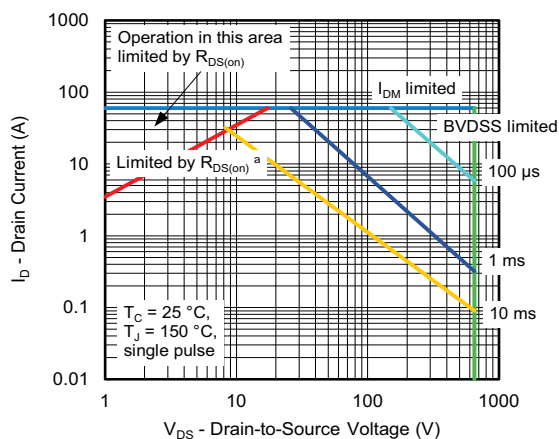
**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.6	

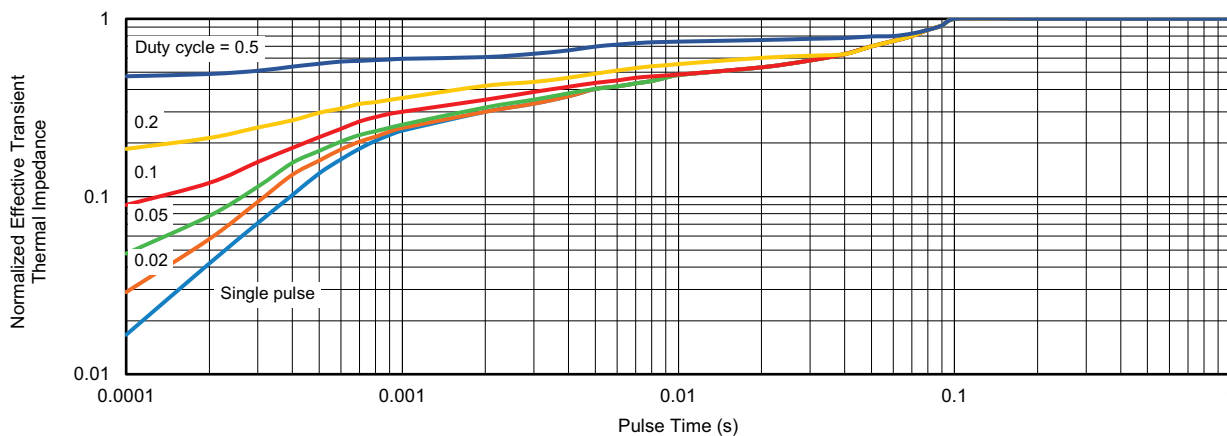
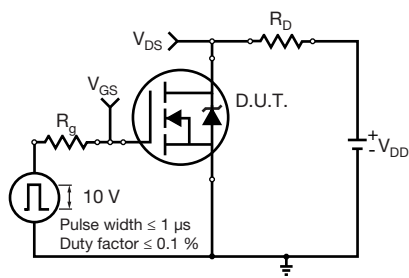
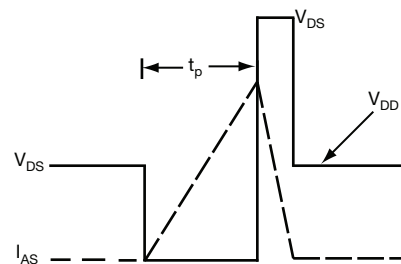
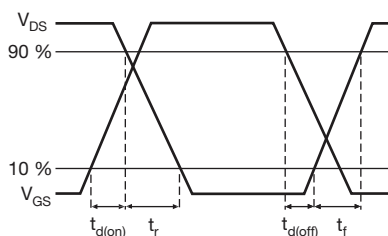
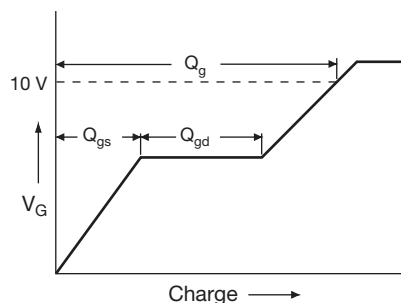
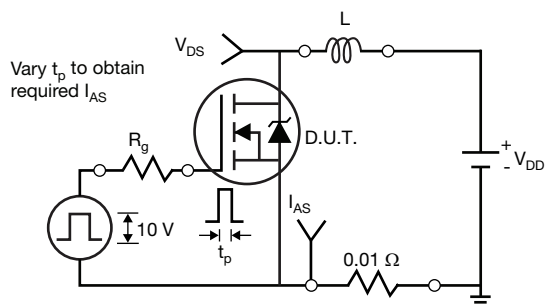
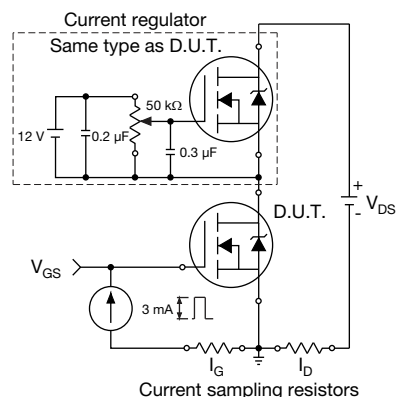
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

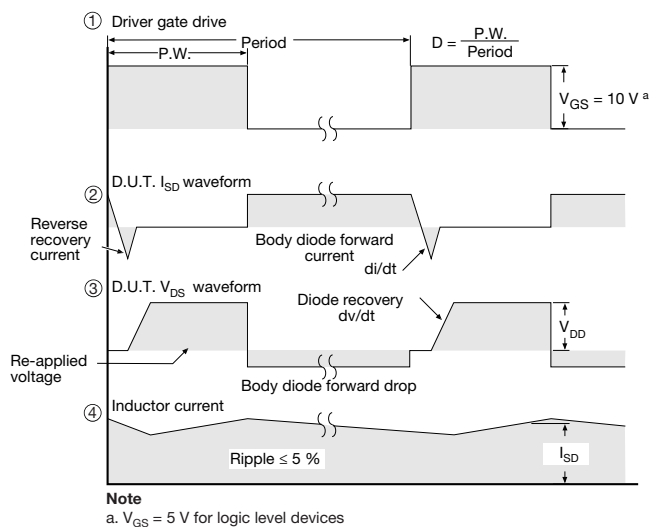
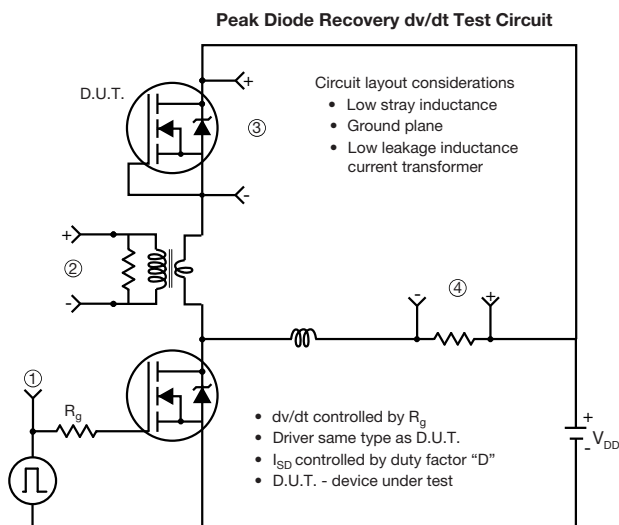
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		650	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.61	-	V/°C
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
		V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	10	
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A	-	0.106	0.120	Ω
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 8 V, I <sub>D</sub> = 12 A		-	11	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 100 kHz		-	1938	-	pF
Output capacitance	C <sub>oss</sub>			-	71	-	
Reverse transfer capacitance	C <sub>rss</sub>			-	2	-	
Effective output capacitance, energy related <sup>a</sup>	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		-	81	-	pF
Effective output capacitance, time related <sup>b</sup>	C <sub>o(tr)</sub>			-	546	-	
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, V <sub>DS</sub> = 520 V	-	38	57	nC
Gate-source charge	Q <sub>gs</sub>			-	15	-	
Gate-drain charge	Q <sub>gd</sub>			-	14	-	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 520 V, I <sub>D</sub> = 12 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	26	52	ns
Rise time	t <sub>r</sub>			-	59	118	
Turn-off delay time	t <sub>d(off)</sub>			-	46	92	
Fall time	t <sub>f</sub>			-	26	52	
Gate input resistance	R <sub>g</sub>	f = 1 MHz, Open Drain		0.4	0.8	1.6	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	25	A
Pulsed diode forward current	I <sub>SM</sub>			-	-	60	
Diode forward voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 12 A, V <sub>GS</sub> = 0 V		-	-	1.2	V
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 12 A, di/dt = 100 A/μs, V <sub>R</sub> = 25 V		-	345	690	ns
Reverse recovery charge	Q <sub>rr</sub>			-	4.4	8.8	μC
Reverse recovery current	I <sub>RRM</sub>			-	22	-	A

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Temperature vs. Drain-to-Source Voltage**

**Fig. 9 - Maximum Safe Operating Area**
**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified


**Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case**

**Fig. 13 - Switching Time Test Circuit**

**Fig. 16 - Unclamped Inductive Waveforms**

**Fig. 14 - Switching Time Waveforms**

**Fig. 17 - Basic Gate Charge Waveform**

**Fig. 15 - Unclamped Inductive Test Circuit**

**Fig. 18 - Gate Charge Test Circuit**



**Fig. 19 - For N-Channel**

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